# onsemi

## NPN Darlington Transistor PZTA28, MMBTA28

#### Description

This device is designed for applications requiring extremely high current gain at collector currents to 500 mA. Sourced from process 03.

#### Features

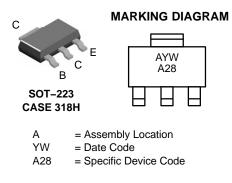
• These are Pb–Free Devices

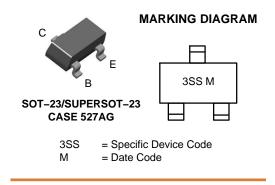
## **ABSOLUTE MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Note 1, Note 2)

Symbol	Parameter	Value	Unit
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	12	V
Ι <sub>C</sub>	I <sub>C</sub> Collector Current – Continuous		mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	–55 to + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.





#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
PZTA28	SOT-223	4000 / Tape & Reel
MMBTA28	SOT-23	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## PZTA28, MMBTA28

#### **THERMAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

		Мах		
Symbol	Parameter	PZTA28 (Note 3)	MMBTA28 (Note 4)	Unit
PD	Total Device Dissipation	1000	350	mW
	Derate Above 25°C	8.0	2.8	mW/°C
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient	125	357	°C/W

3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

4. Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6cm<sup>2</sup>.

#### **ELECTRICAL CHARACTERISTICS** (Note 5) ( $T_A = 25^{\circ}C$ unless otherwise noted)

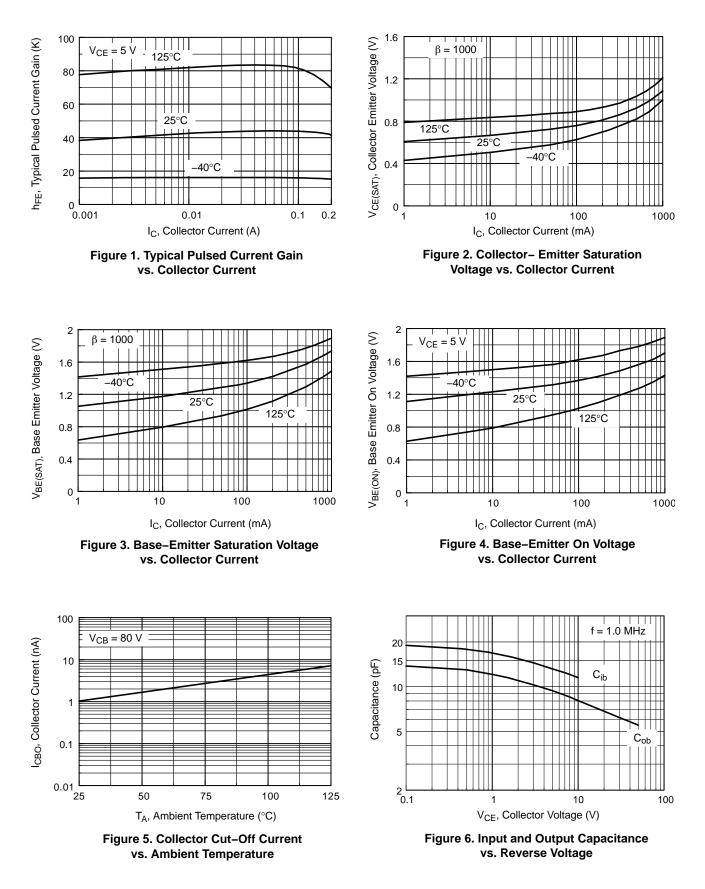
Symbol	Parameter	Test Conditions	Min	Max	Unit
V <sub>(BR)CES</sub>	Collector–Emitter Breakdown Voltage	$I_{C} = 100 \ \mu A, \ V_{BE} = 0$	80		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	80		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	12		V
I <sub>CBO</sub>	Collector Cut–Off Current	$V_{CB} = 60 \text{ V}, I_E = 0$		100	nA
I <sub>CES</sub>	Collector Cut–Off Current	$V_{CE} = 60 \text{ V}, \text{ V}_{BE} = 0$		500	nA
I <sub>EBO</sub>	Emitter Cut–Off Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		100	nA
h <sub>FE</sub>	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10000		
		$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10000		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.01 mA		1.2	V
		$I_{\rm C} = 100$ mA, $I_{\rm B} = 0.1$ mA		1.5	
V <sub>BE(on)</sub>	Base–Emitter On Voltage	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 5.0 V		2.0	V
f <sub>T</sub>	Current Gain – Bandwidth Product	$I_{C}$ = 15 mA, $V_{CE}$ = 5.0 V, f = 100 MHz	125		MHz
C <sub>obo</sub>	Output Capacitance	$V_{CB}$ = 1.0 V, I <sub>E</sub> = 0, f = 1.0 MHz		8.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2.0%.

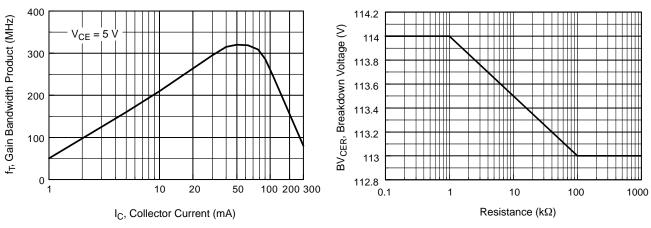
### PZTA28, MMBTA28

### **TYPICAL PERFORMANCE CHARACTERISTICS**



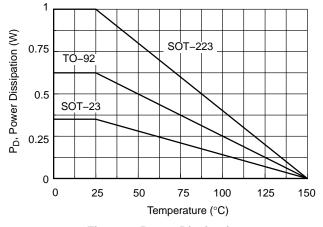
## PZTA28, MMBTA28

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)











SOT-223 CASE 318H ISSUE B DATE 13 MAY 2020 A NDTES SCALE 2:1 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009. CONTROLLING DIMENSION: MILLIMETERS DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS DG GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE. LEAD DIMENSIONS & AND &1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBBAR PROTRUSION IS 0.08mm PER SIDE. DATUMS A AND B ARE DETERMINED AT DATUM H. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS & AND &1. DIMENSIONING AND TOLERANCING PER ASME 1. b1 2 з. В 4. 5. 6. 7. b AND b1. MILLIMETERS DIM MIN. NITM. MAX. e \_\_\_ \_\_\_ 1.80 k Α  $\oplus$  0.10  $\otimes$  C A B 0.02 0.06 0.11 A1 TOP VIEW NDTE 7 0.60 0.74 0.88 b 2.90 3.10 b1 3.00 DETAIL A 0.24 \_\_\_\_ 0.35 С H 6.70 D 6.30 6.50 Ε 6.70 7.00 7.30 E1 3.30 3.50 3.70 0.10 C 2.30 BSC e SIDE VIEW FND VIEW L 0.25 \_\_\_ i 10° 0° \_\_\_\_ -3.80 2.00 Α1 DETAIL A 8.30 3x= Assembly Location GENERIC A 2.00 **MARKING DIAGRAM\*** Y = Year = Work Week w XXXXX = Specific Device Code = Pb-Free Package 5'30 AYW 3x 1.50 (Note: Microdot may be in either location) XXXXX= PITCH \*This information is generic. Please refer to RECOMMENDED MOUNTING FOOTPRINT device data sheet for actual part marking. For additional information on our Pb-Free strategy Pb-Free indicator, "G" or microdot "•", may ж and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D. or may not be present. Some products may not follow the Generic Marking. Electronic versions are uncontrolled except when accessed directly from the Document Repository. **DOCUMENT NUMBER:** 98ASH70634A Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DESCRIPTION:** SOT-223 PAGE 1 OF 1

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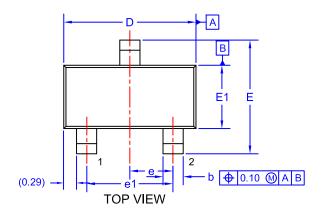
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### **MECHANICAL CASE OUTLINE** PACKAGE DIMENSIONS



#### SOT-23/SUPERSOT <sup>™</sup> -23, 3 LEAD, 1.4x2.9 CASE 527AG **ISSUE A**

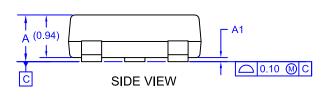
#### DATE 09 DEC 2019

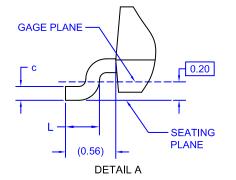


<ol> <li>ASME Y14.3M, 2009.</li> <li>ALL DIMENSIONS ARE IN MILLIMETERS.</li> <li>DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.</li> </ol>				
DIM MIN. NOM. MAX.				
А	0.85	0.95	1.12	
A1	0.00	0.05	0.10	
b	0.370	0.435	0.508	
с	0.085	0.150	0.180	
D	2.80	2.92	3.04	
Е	2.31	2.51	2.71	
E1	1.20	1.40	1.52	
е	0.95 BSC			
e1	1.90 BSC			
L 0.33 0.38 0.43				

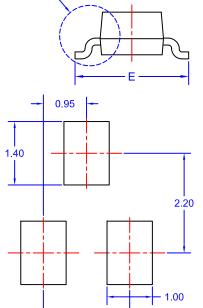
NOTES: UNLESS OTHERWISE SPECIFIED

1. DIMENSIONING AND TOLERANCING PER









LAND PATTERN RECOMMENDATION\* \*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

- 1.90 -

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may

DESCRIPTION:	SOT-23/SUPERSOT-23, 3 LEAD, 1.4X2.9		PAGE 1 OF 1	
DOCUMENT NUMBER:	98AON34319E	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
•	(Note: Microdot may be in	either location) not follow the Generic Marking.		

XXX = Specific Device Code

= Pb-Free Package

= Month Code

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GENERIC **MARKING DIAGRAM\*** 

XXXM=

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